













New trends in isotopic identification with telescope detectors

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Needs for isotopic identification

EoS and isospin transport

Isospin effects in nuclear reactions Recent results from ISOFAZIA experiment Study of the N=Z fragment production Equilibration dynamics and isospin effects Isospin influence on IMF dynamical emission Constrains on the symmetry energy Equilibration chronometry and reaction dynamics Dynamical properties and secondary decay

(S.Yennello)

(S.Piantelli)

(A.Camaiani)

(A.S. Umar)

(B. Gnoffo)

(J. Lukasik)

(A. Rodriguez)

(W. Trautmann)

Clusters in structure and dynamics

Characterization of the nuclear gas phase Transport properties at Fermi energies Probing nucleon-nucleon correlations Temperature and densities of hot ⁴⁰Ca, ⁴⁰Si Influence of neutron enrichment on de-excitation (P. St Onge) Exotic clustering investigation in ¹³B, ¹⁴C Decay of ¹²C excited states Study of four reactions forming 46Ti*

(E. Bonnet)

(M.Henry) (S. Szilner)

(K. Schmidt)

(A. Di Pietro)

(L. Quattrocchi)

(M. Cicerchia)

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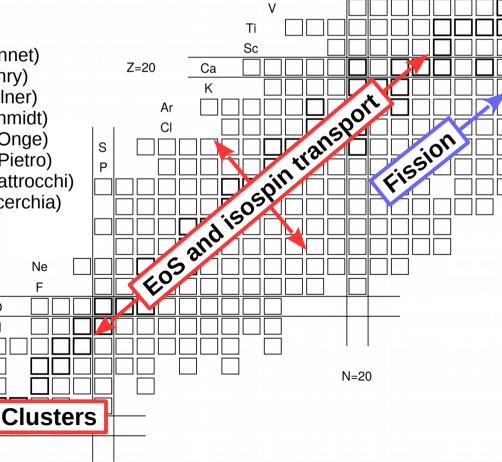
С В

Ве

He Н

Fission

Fission in inverse kinematics 1 (M. Caamano) Fission in inverse kinematics 2 (L. Audouin)



Cr

 Mn_1

1 Δ E-E identification

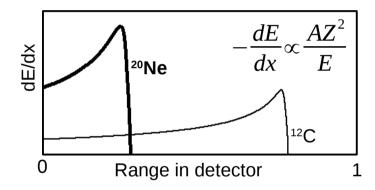
Pulse Shape Analysis identification

3 Time of Flight identification

4 Data processing

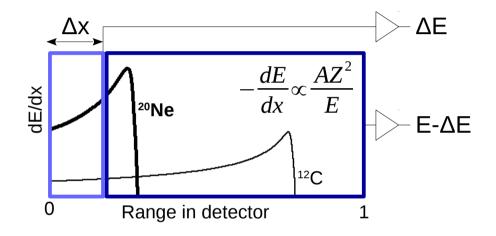
Stopping power

Stopping power depends on the charge (Z), mass (A), and energy (E) of the particle



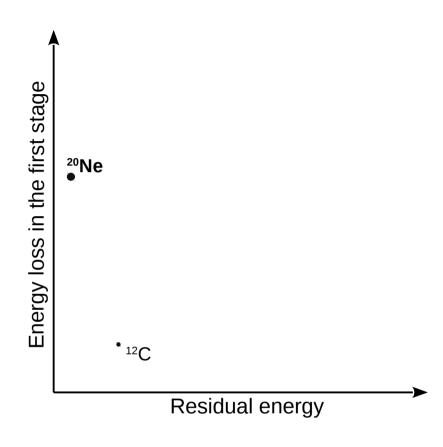
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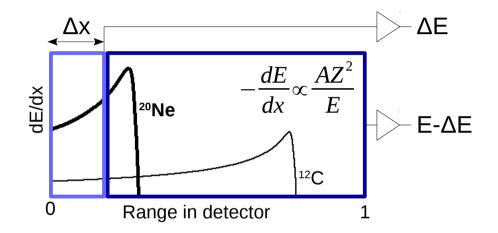
ΔE-E method

Divide the material in ΔE and E layers In the ΔE -E plot, particles populate lines characteristic of their charge and mass



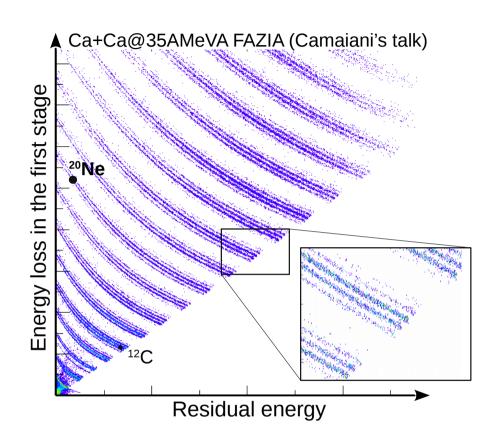
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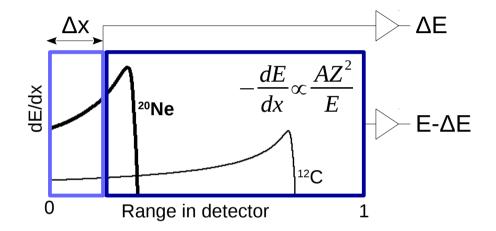
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Stopping power

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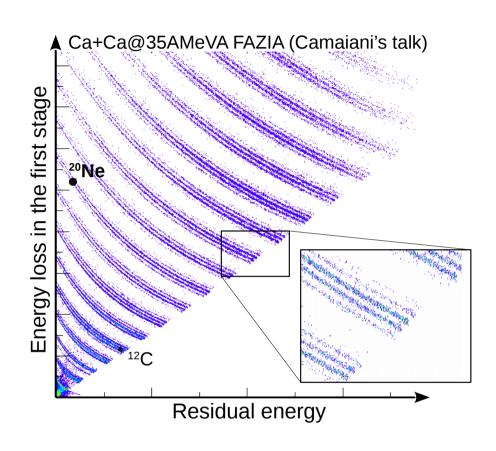


ΔE-E method

Divide the material in ΔE and E layers In the ΔE -E plot, particles populate lines characteristic of their charge and mass

Performances

No limit in charge ID (up to Z~92) Energy straggling limits mass ID (Z<25-30) Limited number of isotopes (~7) per element



Measure ΔE and E

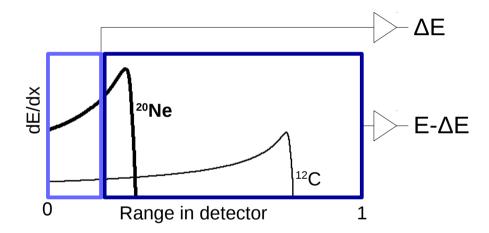
Electronics and signal processing Channeling effects in ΔE detector

Keep Δx under controlDetector thickness homogeneity

ΔE-E telescopes

Silicon detectors

Good energy resolution and fast signals (ToF)
Good performances for Pulse Shape Analysis
Can be divided in strips on both side
Often used as thin ΔE layer (from few μm to few mm)



Scintillators

Robust and cheap very thick detectors (few cm)
Mainly CsI(Tl) are used for many years
Neutron sensitive plastic scintillator (Pagano's talk)

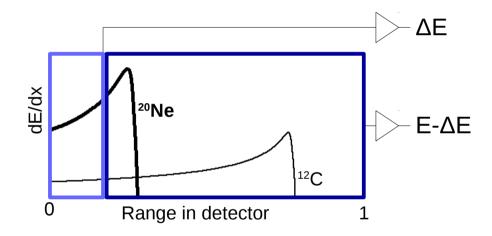
Low pressure gas detectors

Not suitable for isotopic identification (E resolution)

ΔE-E telescopes

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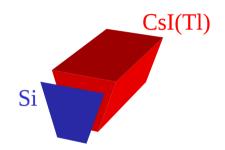
Low pressure gas detectors

Not suitable for isotopic identification (E resolution)

« Simple » telescopes

CHIMERA : Si-CsI FAZIA : Si-Si-CsI

NIMROD : Si-Si-CsI



Silicon strip telescopes

HiRA : Si-Si-Csl

OSCAR : Si-Si

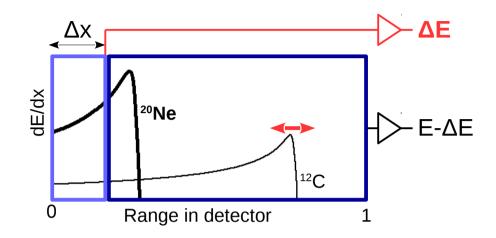
GASPAR : Si-Si-Si FARCOS : Si-Si-CsI

Less simple telescopes

KRATTA: Si-Si-CsI-CsI-Si

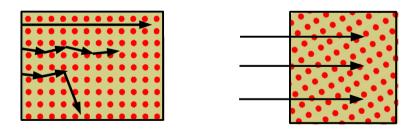


Cristal orientation and channeling



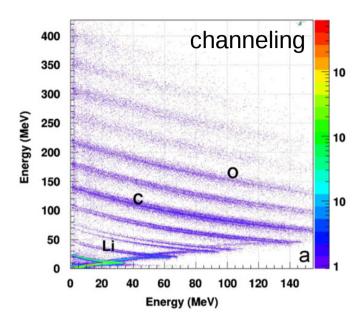
Channeling in silicon

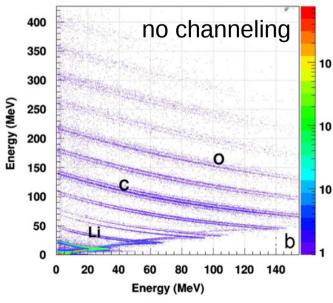
Observed particles goes parallel to the principal axis Induce a fluctuation on the particle range Increases the energy straggling in the ΔE silicon



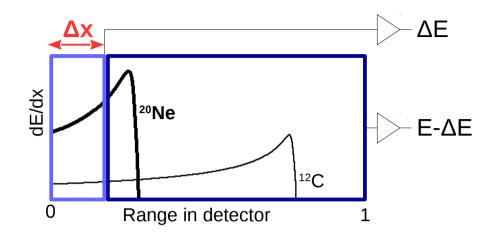
Solution

Cutting the cristal at ~7° with respect to the principal axis allows to recover the isotopic resolution



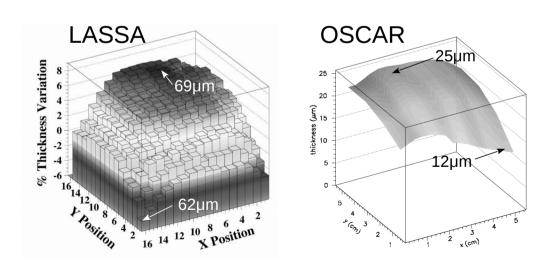


ΔE detector thickness



Thickness homogeneity

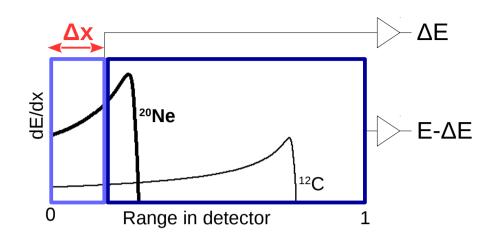
Detector thickness uniformity of few μm ~1% for 500μm, ~10% for 50μm, ~50% for 20μm



Consequence

No mass ID with large area thin silicon detectors

ΔE detector thickness

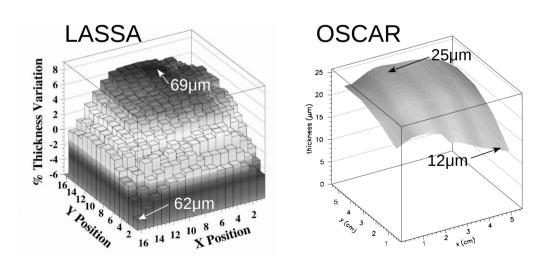


Stripped detectors

Small thickness non-uniformity inside a strip. Can be measured and corrected individually.

Thickness homogeneity

Detector thickness uniformity of few μm ~1% for 500 μm , ~10% for 50 μm , ~50% for 20 μm



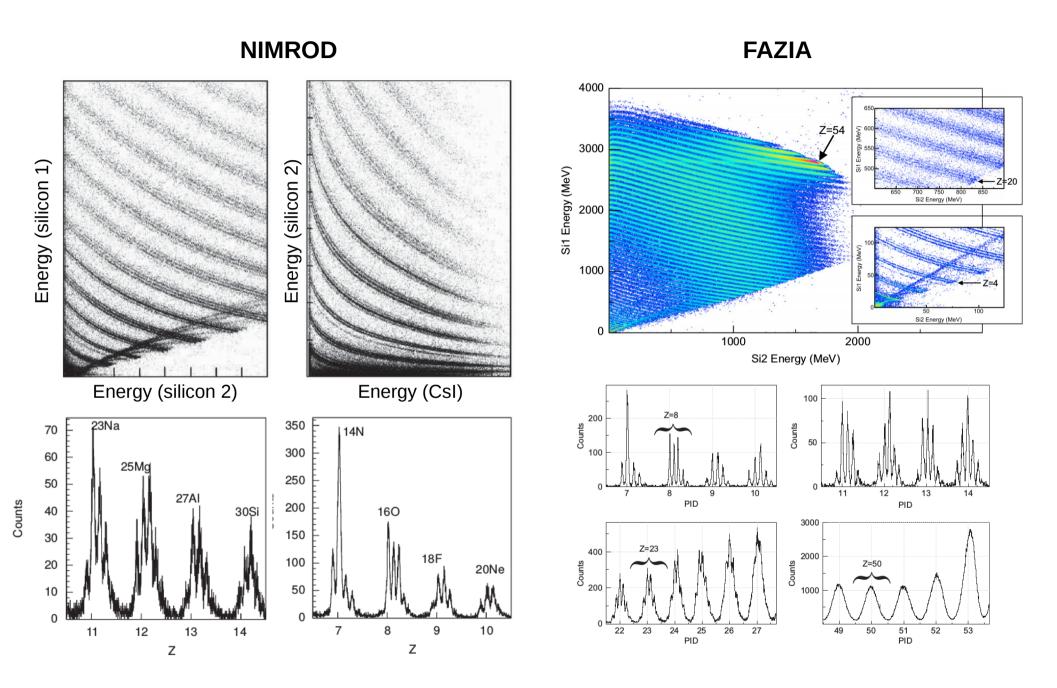
100 125 150 175 200 EF₅₀₀ (MeV) Thickness correction ∆E₆₅ (arbitrary units) 75 100 125 150 175 200 EF₅₀₀ (arbitrary units)

Consequence

No mass ID with large area thin silicon detectors

Davin, NIMA **473** (2001) 302 Dell'Aquila, NIMA **877** (2018) 227

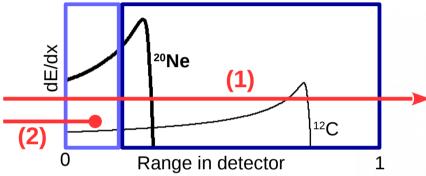
ΔE -E identification : two examples



ΔE -E identification

Basic idea

Divide the material in ΔE and E layers Z and A lines appear in the ΔE -E correlation



Important points

Precise measurement of ΔE and E Avoid channeling effects ΔE detector thickness uniformity

Performances with FAZIA

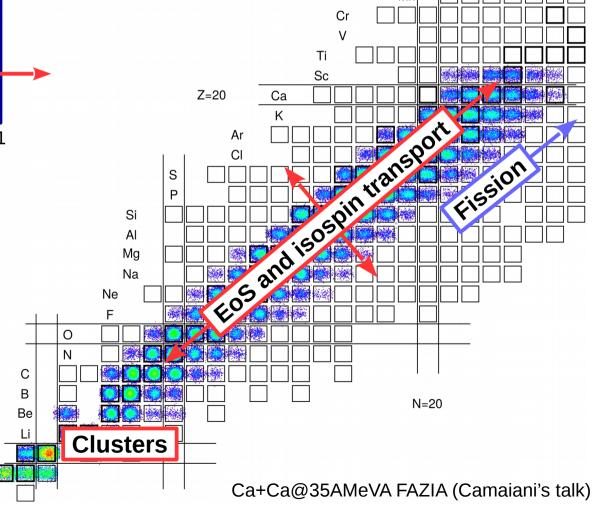
Full charge identification Isotopic identification up to Z~25

He

Limitations

Limited number of A per element (~7) Only particles stopped in the 2nd layer

Solution (1): add a 3rd layer Solution (2): PSA and ToF



1 Δ E-E identification

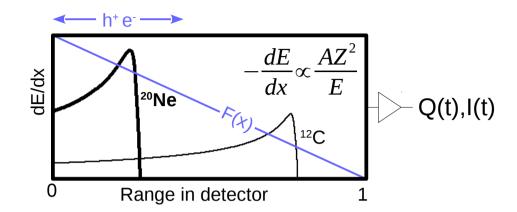
Allows full Z identification and A identification up to $Z\sim25$ Limited number of isotopes per element (~7) Works only for particles punching through the first layer

Pulse Shape Analysis identification

3 Time of Flight identification

4 Data processing

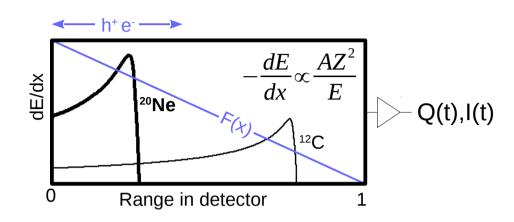
Pulse Shape Analysis in silicon detectors



Stopping power (again)

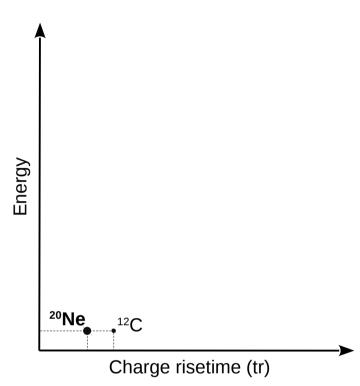
Two ions with the same energy but different charge and/or mass have different energy loss profiles

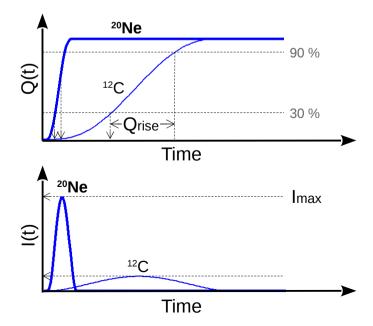
Pulse Shape Analysis in silicon detectors



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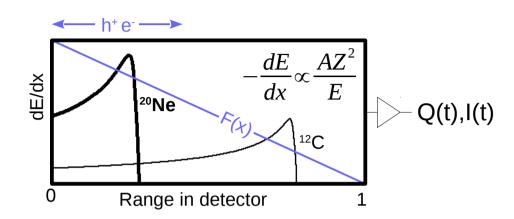




Pulse shape analysis

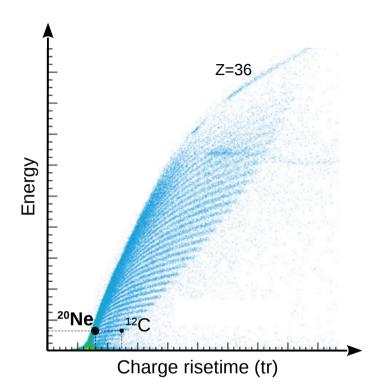
Use the shape of the signal induced by the charge collection to measure Z (and A)
No clear limit for charge identification

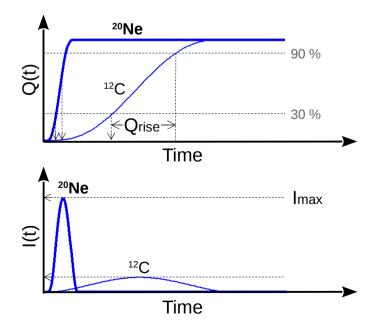
Pulse Shape Analysis in silicon detectors



Stopping power (again)

Two ions with the same energy but different charge and/or mass have different energy loss profiles





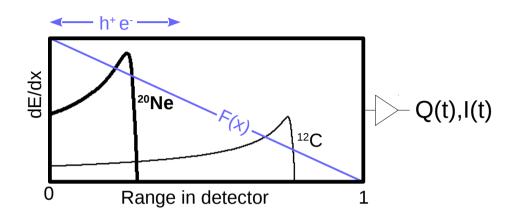
Pulse shape analysis

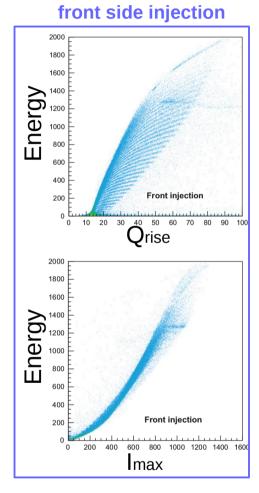
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Important points

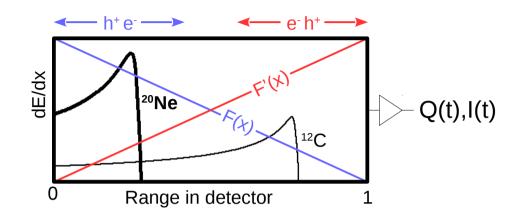
Precise energy measurement
Preserve/characterize the signal shape s(t)
Electric field homogeneity and stability

Pulse Shape Analysis: front or rear injection?





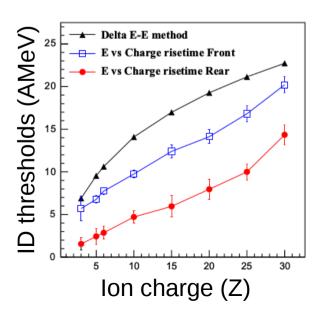
Pulse Shape Analysis: front or rear injection?



Rear side injection

Particles injected in the low field side

Slower signal for low energy heavy ions



front side injection rear side injection Rear injection 1800 1600 Energy 1000 400 Front injection 10 20 20 40 60 80 100 120 140 160 180 200 220 Orise Orise 2000 1800 1800 1600 Energy 1400 1400 1200 1000 600 Front injection 600 800 1000 1200 1400 160 200 400

Advantages

Lower identification thresholds in rear injection Allows to use Imax which gives better mass ID Slower signals are worth for timing (Valdrè's talk)

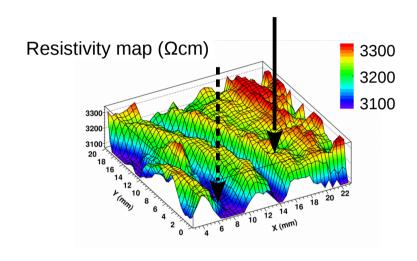
Imax

Imax

Electric field homogeneity and stability

Homogeneity and stability

Collection time should be indepedent of impact position or time. Homogeneous resistivity over the detector surface and constant bias voltage.

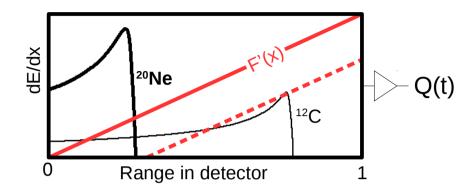


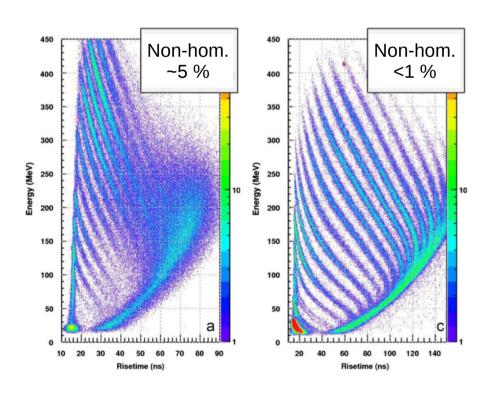
Resitivity mapping

Non-destructive method for resistivity mapping based on Pulse Shape Analysis. Much better performances with < 1% non-homogeneity.

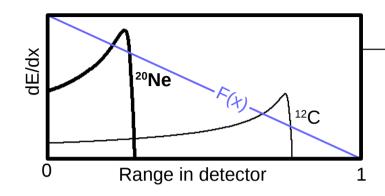
Radiation damage

Leakage current increases in time due to radiation damage. Bias voltage correction.



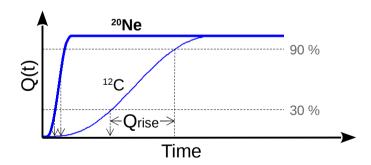


Pulse Shape Analysis in silicon: CHIMERA



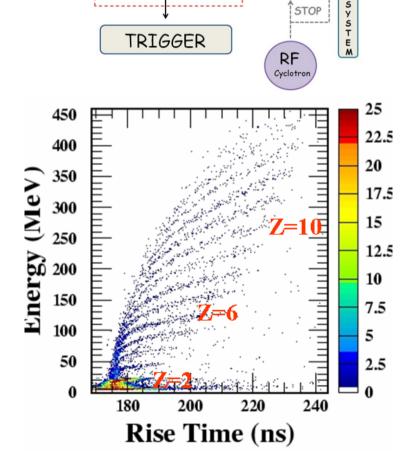
CHIMERA strategy

Front side injection silicons (better for timing) Two CFD (30 % and 80 %) after amplification No digitalization of the signal



Performances

Charge identification No isotopic identification → time of flight



AMP

CAMAC 16ch

CFD 30%

CFD 80%

TRIGGER

Time

PA

PULSER

DATA

QDO

TDC 1

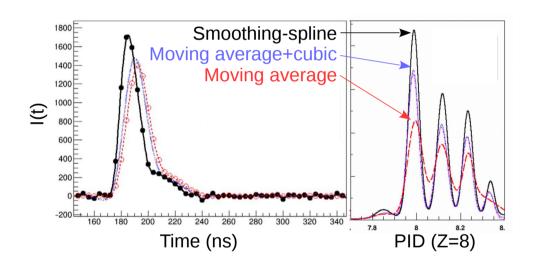
TDC 2

START2

Pulse Shape Analysis in silicon : FAZIA

FAZIA strategy

Reverse mounted nTD silicons (300µm) I(t) sampled at 250MHz and processed offline Energy from a trapezoidal shaper in the FPGA Real-time leackage current auto-correction

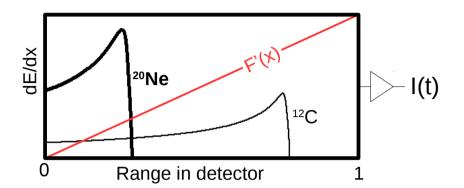


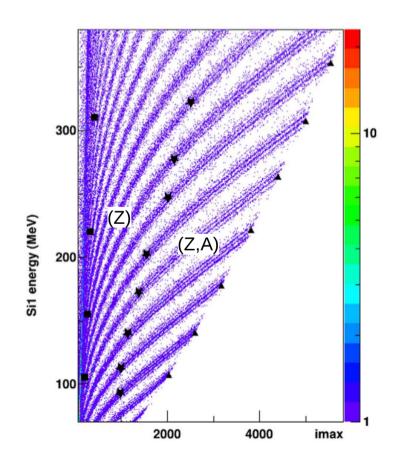
Signal processing

Moving average or smoothing (noise reduction) with cubic or spline interpolation

Optimal filter

Smoothing-spline filter on current signal allows for isotopic identification with low thresholds

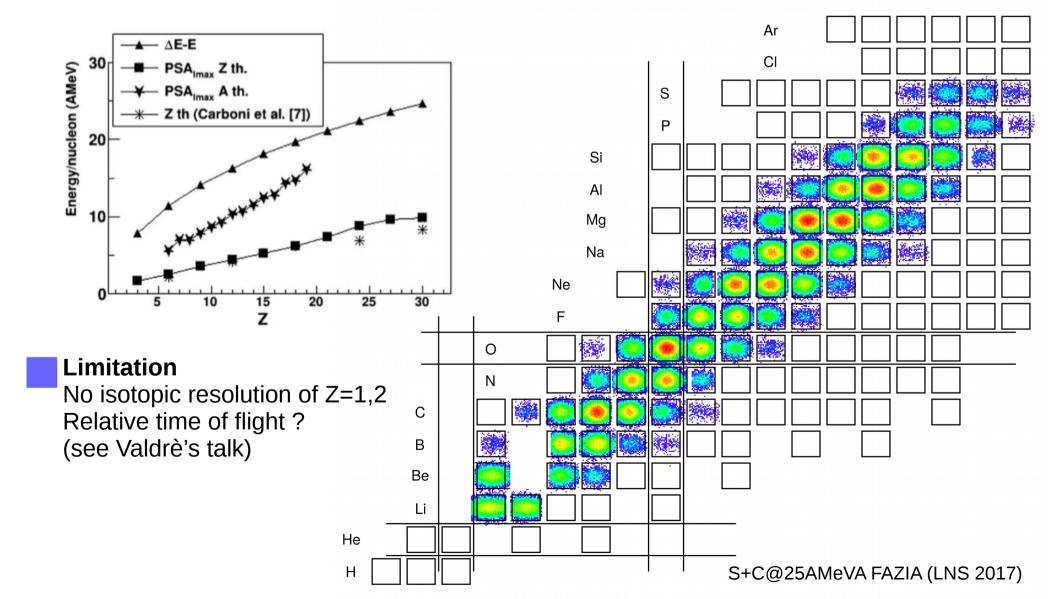




Pulse Shape Analysis in silicon : FAZIA

Performances

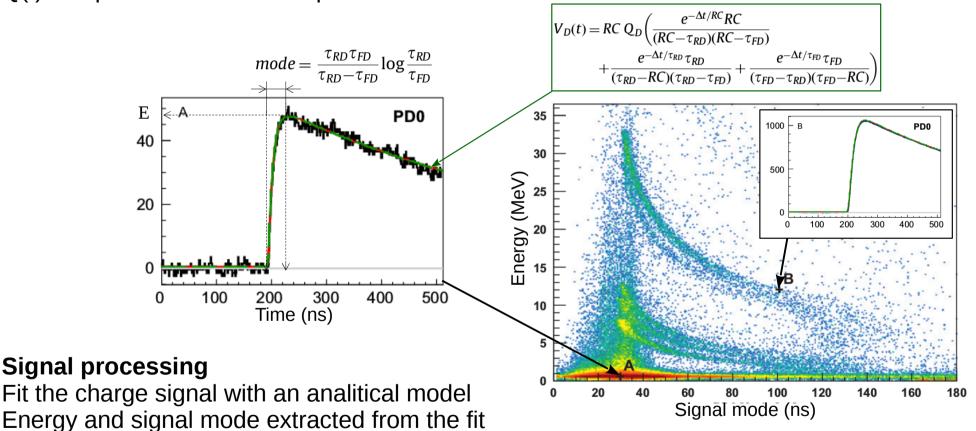
Isotopic identification for 2<Z<20 Z and A identification thresolds reduced



Pulse Shape Analysis in silicon : KRATTA

KRATTA strategy

Reverse mounted silicon photodiodes (500µm) Q(t) sampled at 100MHz and processed offline



Performances

Isotopic identification of light clusters Low identification thresholds

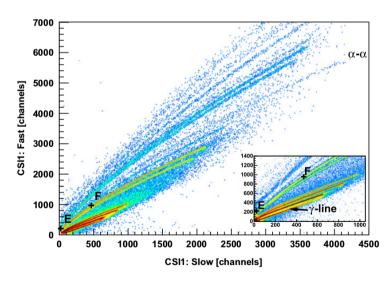
Pulse Shape Analysis: single chip telescope

Concept

Use the silicon for ΔE measurement and scintillation light collection. Both ΔE and E are derived from the silicon signal reducing the complexity and the cost of the electronics.

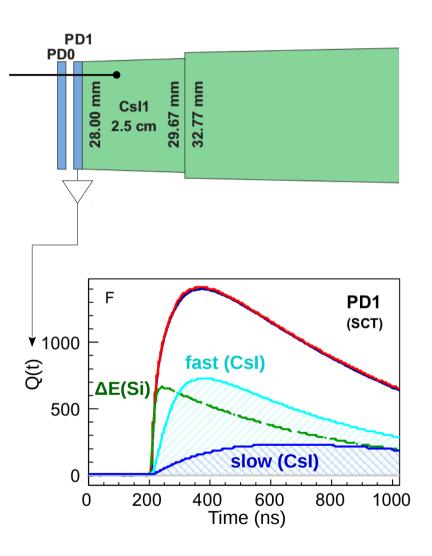
Signal processing

Applying different shapers on Q(t) signal (FAZIA) Fitting the Q(t) signal with a model (KRATTA)



Performances

Both methods give isotopic identification in ΔE -E The fitting procedure allows to do PSA in the CsI



Pasquali, NIMA **301** (1991) 101 Pasquali, EPJA **48** (2012) 158 Lukazik, NIMA **709** (2013) 120

Pulse Shape Analysis identification in silicon

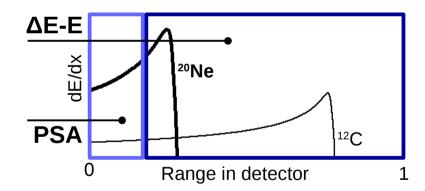
He

Basic idea

Use the shape of the signal induced by the charge collection to measure Z (and A)

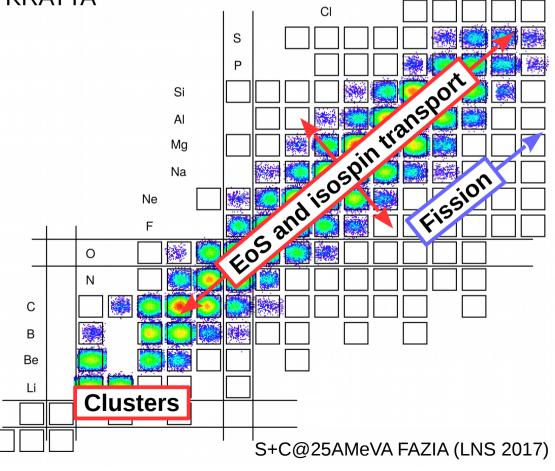
Important points

Better identification in rear injection (worth for timing) Electric field homogeneity and stability are crucial Practical uses: CHIMERA, FAZIA, and KRATTA



Performances with FAZIA

Full charge identification Isotopic identification up to Z~20 Lower identification thresholds



Ar

1 Δ E-E identification

Allows full Z identification and A identification up to Z~25 Limited number of isotopes per element (~7) Works only for particles punching through the first layer

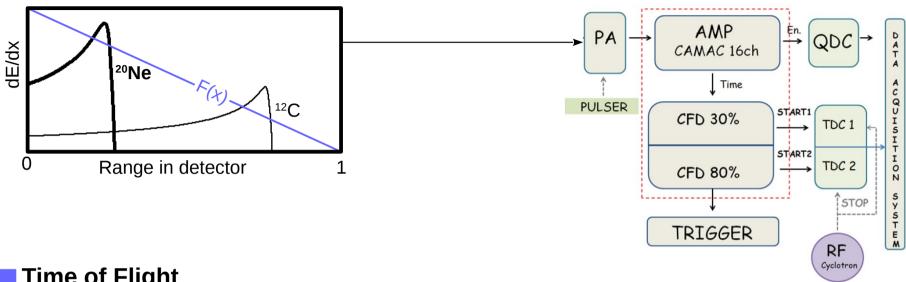
Pulse Shape Analysis identification

Allows full Z identification and A identification up to Z~20 Low charge and mass identification thresholds Many different ways to characterize the signal shape

3 Time of Flight identification

4 Data processing

Time of Flight identification: CHIMERA



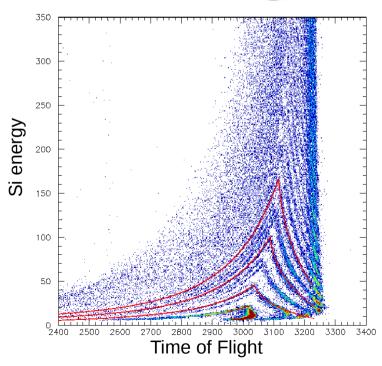
Time of Flight

Deduce the mass from the energy and velocity

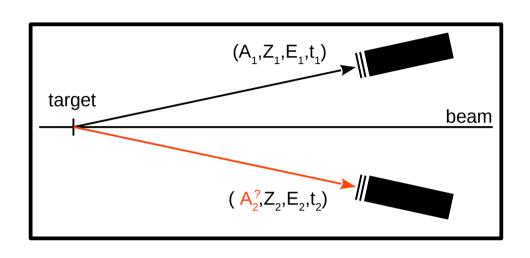
- CHIMERA strategy
 Front side injection silicons (faster signals)
 CFD at 30 % after signal amplification
 Reference time from the cyclotron frequency
- Performances

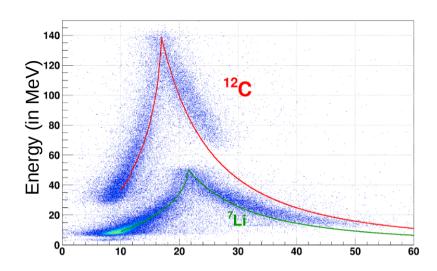
 Mass identification up to A~20

 No charge identification → Pulse Shape Analysis



Time of flight identification: FAZIA





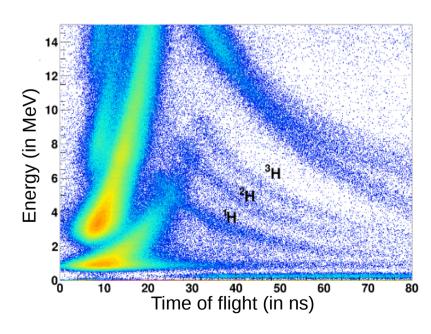
Relative time

Reference time extracted from the time mark of a well identified particle in the same event:

$$ToF_2 = t_2 - t_1 + ToF_1(A_1, E_1)$$

Expected performances

Hope to recover isotopic identification of Z=1,2 stopped in first silicon (Valdrè's talk)



\square \triangle E-E identification

Allows full Z identification and A identification up to Z~25 Limited number of isotopes per element (~7) Works only for particles punching through the first layer

Pulse Shape Analysis identification

Allows full Z identification and A identification up to Z~20 Low charge and mass identification thresholds Many different ways to characterize the signal shape

3 Time of Flight identification

Allows for mass identification only Can be coupled with Pulse Shape Analysis in silicon

4 Data processing

Data processing

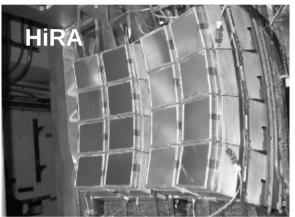
Identification matrices

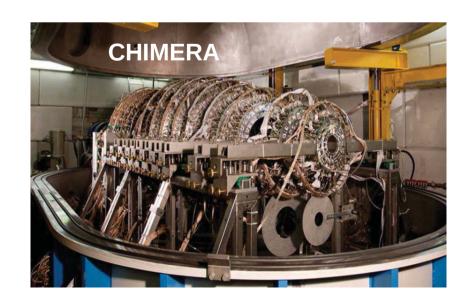
Large arrays made of hundreds of telescopes Several identification matrices per telescopes Matrix complexity increases with increasing isotopic resolution → data reduction more and more difficult and time consuming

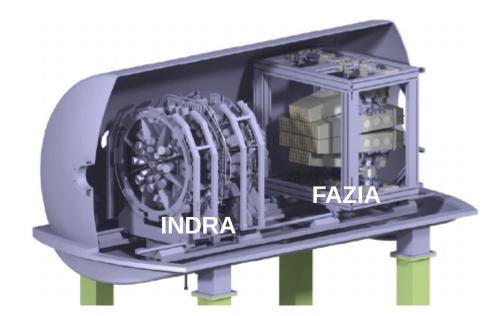
Automatization

Many (semi-)automatic technics: fitting procedures, peak-finding methods, artificial neural netwoks, image processing...









Data processing: evolutionary strategy

Approach

Combines a generative model of ΔE -E relation and a Covariance Matrix Adaptation Evolutionary Strategy (CMA-ES)

Model

Tassan-Got functional (3 free parameters) :

$$\Delta E = \left[(gE)^{\mu + \nu + 1} + \left(\lambda Z^{\alpha} A^{\beta} \right)^{\mu + \nu + 1} + \xi Z^{2} A^{\mu} (gE)^{\nu} \right]^{\frac{1}{\mu + \nu + 1}} - gE$$

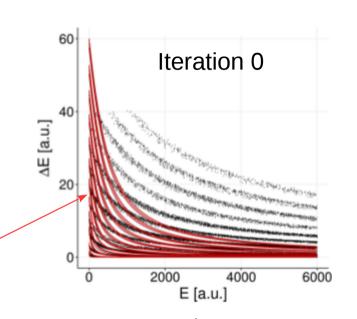
Minimization

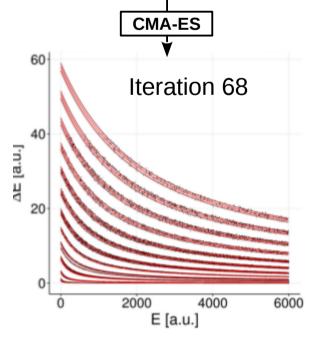
Sum of the distance between each point and the closest line minimized with a CMA-ES method :

$$f(D_{m,2}, g, \mu, \lambda) = \sum_{j=1}^{m} \arg\min_{i \in I} (D_{j,1} - t(D_{j,2}, g, \mu, \lambda, A_i, Z_i))^2$$

Performances

Isotopic identification witout any human intervention Fit result strongly depends on the model quality Only validated on simulated and labeled data





Data processing: from AME to AMI

Approach

Adjust calibration parameters by fitting few clicked (Z,A) lines with the energy loss tables

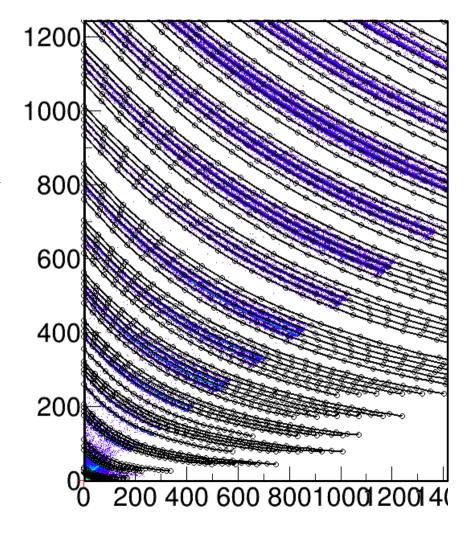
Originality

Very accurate description of silicon detector response and CsI(Tl) light output :

$$\begin{split} L(E) &= -a_G \{ \int_0^{E_\delta} \frac{1}{a_R S_e(E)} \ln \left(1 - \frac{a_R S_e(E)}{1 + a_R S_e(E) + a_n S_n(E)} \right) \frac{dE}{1 + S_n(E)/S_e(E)} \\ &+ \int_{E_\delta}^{E_0} \frac{1 - F(E)}{y(E) a_R S_e(E)} \ln \left(1 - \frac{y(E) a_R S_e(E)}{1 + a_R S_e(E) + a_n S_n(E)} \right) \frac{dE}{1 + S_n(E)/S_e(E)} \\ &- \int_{E_\delta}^{E_0} \frac{F(E) dE}{1 + S_n(E)/S_e(E)} \} \end{split}$$

Performances

Isotopic identification with little human intervention (few lines to be clicked)
Successfully applied on FAZIA Si-Si and Si-CsI(TI) matrices



Data processing: SPIDER identification

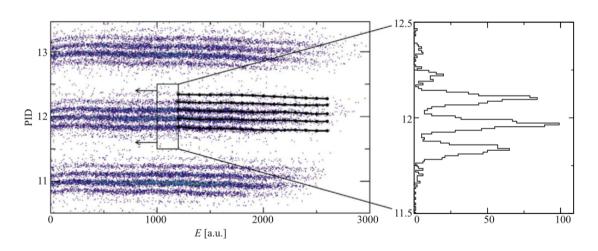
- SPIDER (charge) identification

 Peak-finding method after projection of the matrix

 No assumption on the underlying physics
- SPIDER (mass) identification

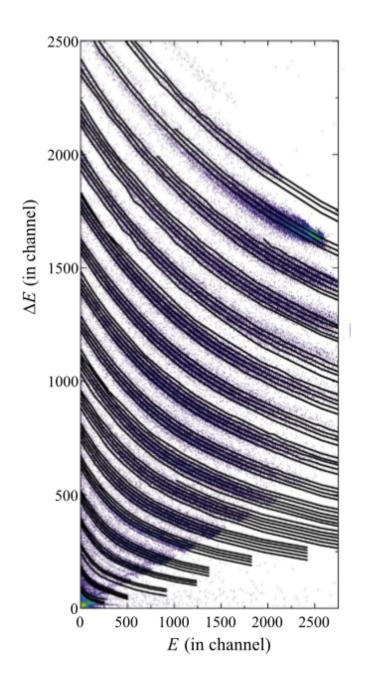
 Peak-finding after matrix linearization/projection

 The only input is the Z identification grid



Performances

Allows for very fast isotopic identification (on-line) Little human intervention (two mouse-clicks) Works with many matrix types (ΔE -E, PSA) Mass ID not precise enough for physics analysis



1 Δ E-E identification

Allows full Z identification and A identification up to Z~25 Limited number of isotopes per element (~7) Works only for particles punching through the first layer

2 Pulse Shape Analysis identification

Allows full Z identification and A identification up to Z~20 Low charge and mass identification thresholds Many different ways to characterize the signal shape

3 Time of Flight identification

Allows for mass identification only Can be coupled with Pulse Shape Analysis in silicon

4 Data processing

Matrix complexity increases with increasing performances New (semi-)automatic methods are welcome

What I forgot...

Electronics

GET electronics (Marchi's talk, De Filipo's and Pagano's talk) Multichannel CMOS front ends (Guazzoni's talk)... FAZIA electronics (Valdrè's talk)

Pulse Shape Analysis

Artificial neural network approach (Flores, NIMA **830** (2016) 287) PSA with stripped detectors (Genolini, NIMA **732** (2013) 87) Pulse Shape Analysis in CsI(Tl)

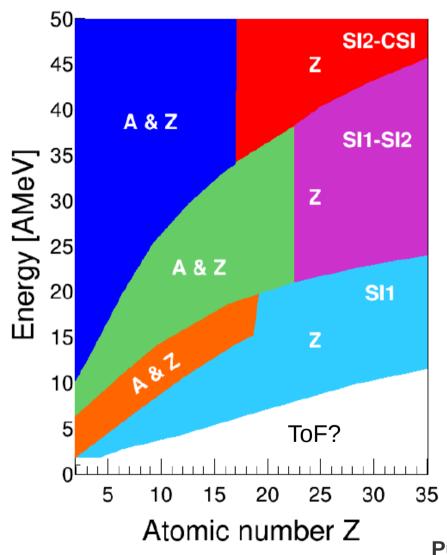
High energies

Fragmentation in detectors (Morfouace, NIMA 848 (2017) 45)

Neutron detection

Neutron sensitive solid scintillator (E. Pagano's talk) Neutron-gamma discrimination...

FAZIA block performances



Identification capabilities.
Full charge identification and isotopic identification up to Z=15-25 depending on the ion velocity.

Low identification thresholds.
Low identification thresholds thanks to pulse shape analysis in the first silicon stage.
Adapted for reaction with beams from 20 MeV/nuc to 150MeV/nuc (GANIL, LNS, GSI).
Could be improved with ToF measurements.

